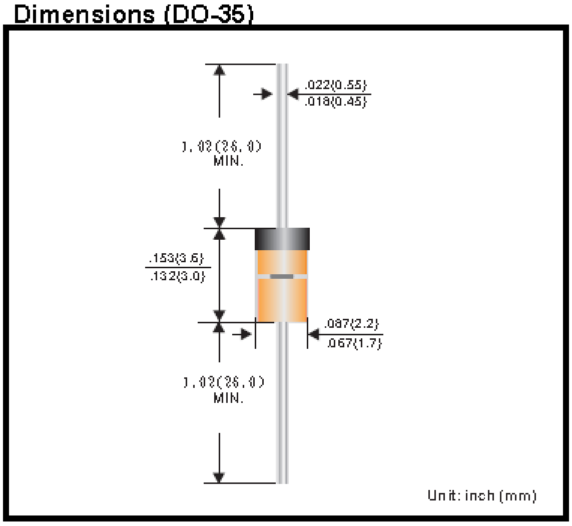
BAV20

Signal Diode

Absolute Maximum Ratings (Ta=25℃)			
Items	**Symbol**	**Ratings**	**Unit**
Reverse Voltage	V_R	200	V
Reverse Recovery Time	T_{rr}	50	ns
Power Dissipation 3.33mW/ ℃ (25℃)	P	500	mW
Forward Current	I_F	250	mA
Junction Temp.	T_j	-65 to 175	℃
Storage Temp.	T_{stg}	-65 to 175	℃

Dimensions (DO-35)



Mechanical Data	
Items	**Materials**
Package	DO-35
Case	Hermetically sealed galss
Lead/ Finish	Double stud/ Solder Plating
Chip	Glass Passivated

Electrical Characteristics (Ta=25℃)			
Parameter	**Symbol**	**Limit**	**Unit**
Breakdown Voltage I_R= 100μA	V_R	200	V
Peak Forward Surge Current PW= 1sec.	I_F surge	1	A
Maximum Forward Voltage I_F= 100mA	V_F	1	V
Maximum Reverse Current V_R= 150V V_R= 150V, T_j= 100℃	I_R	0.1 15	μA
Maximum Junction Capacitance V_R= 0, f= 1 MHz	C_j	1.5	pF
Maximum Reverse Recovery Time I_F=I_R=30mA, V_R= 6V, I_{RR}= 3mA, R_L= 100Ω	T_{rr}	50	ns

Characteristics (T$_j$ = 25°C unless otherwise specified)

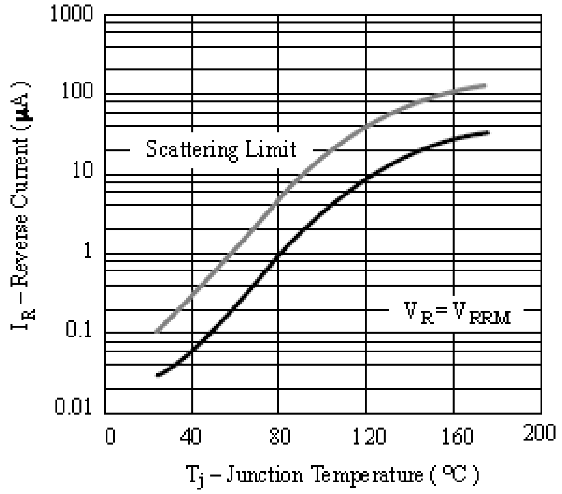


Figure 1. Reverse Current vs. Junction Temperature

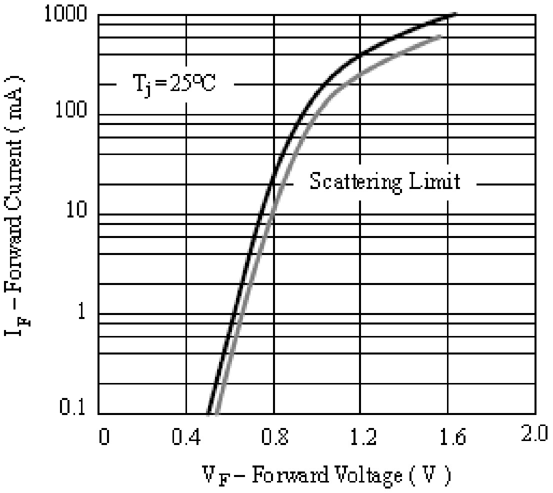


Figure 2. Forward Current vs. Forward Voltage

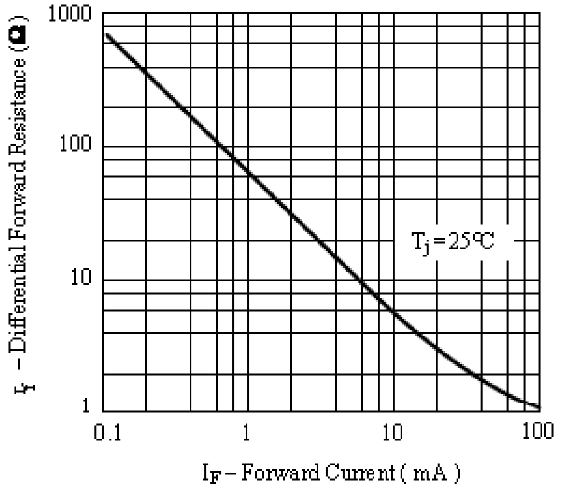


Figure 3. Differential Forward Resistance vs. Forward Current